

Search History (3 pp.) ~~Page 1~~ (9/25/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3	"823244".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:36
S2	491	(257/173).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 18:31
S3	32	S2 and semiconductor near2 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 15:29
S4	52	S2 and zener near2 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 15:30
S5	39	(S2 and zener near2 diode) not S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 15:30
S6	0	("deepadjwellnear10shallowadjwel landesd").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 18:31
S7	0	deep adj well near10 shallow adj well and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 18:32
S8	18	double adj well and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 18:37
S9	1625	((257/355) or (257/356) or (257/357) or (257/358)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/25 00:30
S10	243	S9 and (second deep shallow) adj2 well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 20:29

S11	78	S9 and (second deep shallow) adj2 well and "well" near5 "within" near5 "well"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:12
S12	0	zener adj diode near4 backside near4 substrate and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:13
S13	0	zener adj diode near4 back-side near4 substrate and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:13
S14	0	zener adj diode near6 back-side near6 substrate and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:13
S15	0	zener adj diode near6 back-side near6 substrate and (protecting protection esd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:14
S16	3	diode near6 back-side near6 substrate and (protecting protection esd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 19:14
S17	1875	((257/355) or (257/356) or (257/357) or (257/358) or (257/173) or (257/174)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/05/29 20:28
S18	269	S17 and (second deep shallow) adj2 well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 20:29
S19	188	S17 and (second deep shallow) adj2 well and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 20:29
S20	2	("5932898").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:45

S21	2	("6891207").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:45
S22	1944	((257/355) or (257/356) or (257/357) or (257/358) or (257/173) or (257/174)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/25 00:31
S23	404	S22 and (doping dopant impurity impurities) near6 ("small" "smaller" "lower" "less" "larger" "greater")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/25 00:34
S24	335	S22 and (doping dopant impurity impurities) near6 ("small" "smaller" "lower" "less" "larger" "greater")	USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/09/25 01:09
S25	2	("20030047750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/25 04:21